

1-Line Ultra Low Capacitance Uni-directional TVS Diode

Description

The PESDR3301P0 is an uni-directional TVS diode, to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high--speed data lines. The PESDR3301P0 has an ultra-low capacitance with a typical value at 0.45pF, and complies with the IEC61000-4-2 (ESD) standard with ±20kV air and ±20kV contact discharge. It is assembled into an ultra-small 0.6x0.3x0.3mm lead-free DFN package. The small size, ultra-low capacitance and high ESD surge protection make PESDR3301P0 an ideal choice to protect cellphone, digital video interfaces, HDMI, DVI, USB2.0, USB3.0 and other high speed ports.

Features

- Ultra low capacitance: 0.45pF
- Low operating voltage: 3.3V
- Low clamping voltage
- 2-pin leadless package
- Complies with following standards:
 - -IEC 61000-4-2 (ESD) immunity test

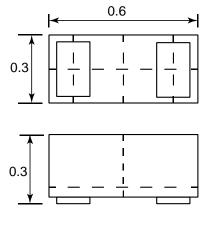
Air discharge: ±20kV

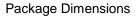
Contact discharge: ±20kV

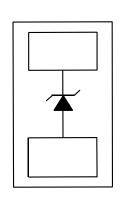
—IEC 61000-4-5 (Lightning) 4A (8/20μs)

RoHS Compliant

Dimensions and Pin Configuration







Circuit and Pin Schematic

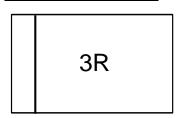
Mechanical Characteristics

- Package: DFN0603-2 (0.6×0.3×0.3mm)
- Case Material: "Green" Molding Compound.
- Moisture Sensitivity: Level 1 per J-STD-020
- Marking Information: See Below

Applications

- Cellular Handsets and Accessories
- Display Ports
- MDDI Ports
- USB Ports
- Digital Video Interface (DVI)
- PCI Express and Serial SATA Ports

Marking Information



3R= Device Marking Code Bar denotes cathode

Ordering Information

Part Number	Shipping	Reel Size
PESDR3301P0	10000/Tape & Reel	7 inch



Absolute Maximum Ratings (TA=25°C unless otherwise specified)

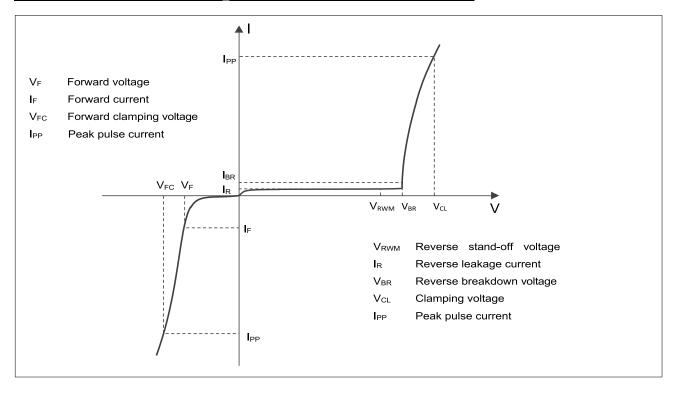
Parameter	Symbol	Value	Unit	
Peak Pulse Power (8/20μs)	P _{PK}	56	W	
Peak Pulse Current (8/20µs)	Ірр	4	А	
ESD per IEC 61000-4-2 (Air)	V	±20	127	
ESD per IEC 61000-4-2 (Contact)	V _{ESD}	±20	- kV	
Lead temperature	T∟	260	°C	
Operating Temperature Range	Тор	-40 ~ + 85	°C	
Storage Temperature Range	T _{STG}	−55 ~ + 150	°C	

Electrical Characteristics (TA=25°C unless otherwise specified)

Parameter	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse Working Voltage	V_{RWM}			3.3	V	
Breakdown Voltage	V_{BR}	4.0	4.8		V	$I_T = 1 \text{mA}$
Reverse Leakage Current	I _R			0.1	μA	V _{RWM} = 3.3V
Forward Voltage	VF			1.2	V	I _F =15mA
Clamping Voltage	Vc			10	V	I _{PP} = 1A (8/20µs pulse),
Clamping Voltage	Vc			14	V	I _{PP} = 4A (8/20µs pulse),
Junction Capacitance	С		0.45	0.8	pF	$V_R = 0V$, $f = 1MHz$



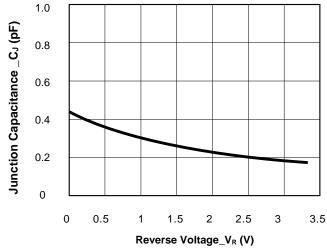
Electrical characteristics (T_A = 25°C, unless otherwise noted)

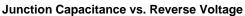


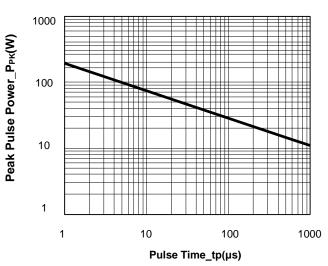
Definitions of electrical characteristics



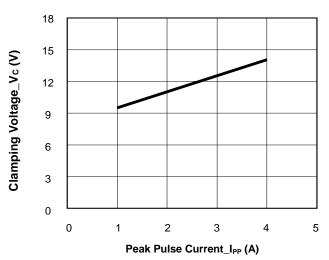
Typical Performance Characteristics (TA=25°C unless otherwise Specified)



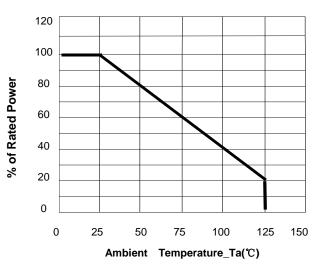




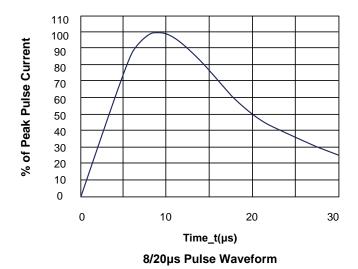
Peak Pulse Power vs. Pulse Time



Clamping Voltage vs. Peak Pulse Current

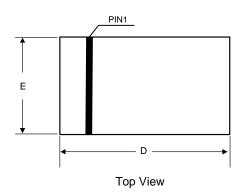


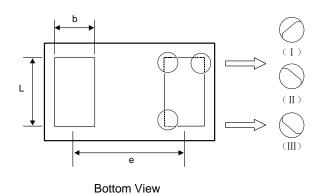
Power Derating Curve

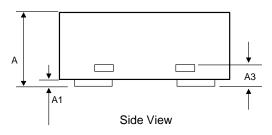




DFN0603-2 Package Outline Drawing

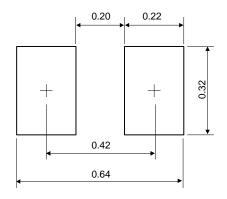






	Dimensions in Millimeters			
Symbol	Min.	Тур.	Max.	
А	0.230	0.300	0.350	
A1	0.000	-	0.050	
A3	0.102REF.			
D	0.550	0.600	0.670	
E	0.250	0.300	0.370	
b	0.160	0.190	0.230	
L	0.215	0.245	0.275	
e	0.360 BSC			

Recommended PCB Layout (Unit: mm)



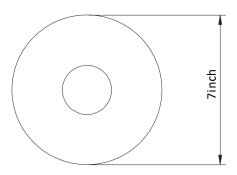
Notes:

This recommended land pattern is for reference purposes only. Please consult your manufacturing group to ensure your PCB design guidelines are met.

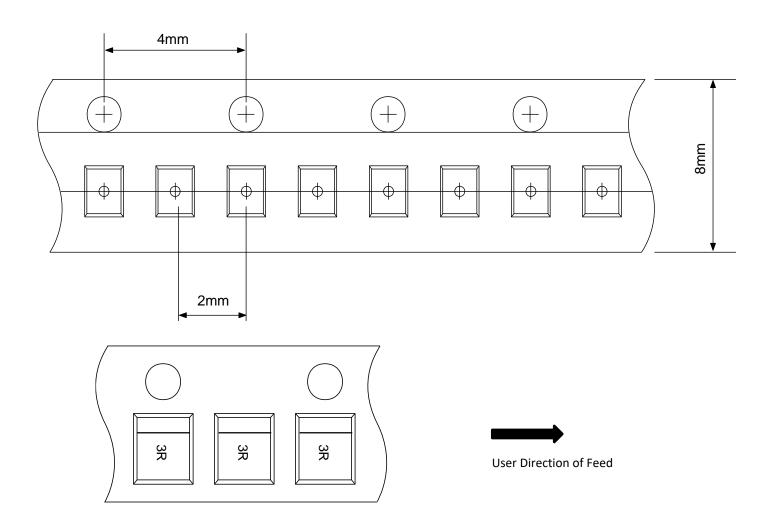


TAPE AND REEL INFORMATION





Tape Dimensions





IMPORTANT NOTICE

The information given in this document is believed to be accurate and reliable but shall in no event be regarded as a guarantee of conditions or characteristics.PN-Silicon assumes no responsibility for any errors in this document, or for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of PN-Silicon.

The product listed in this document are designed to be used with ordinary electronic equipment or devices and are not authorized to used with equipment or devices which require an extremely high level of reliability and the malfunction of with would directly endanger human life (such as medical instruments, aerospace machinery, nuclear-reactor controllers, automotive and other safety device.)

The PN SILICON logo is a registered trademark of PN-Silicon co., ltd which reserves the right to make changes to the product or this document at any time without notice. Buyers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. PN-Silicon makes no warranty, representation or guarantee, express or implied, regarding the suitability of its products for any particular purpose. All rights reserved.